

英飞凌MOSFET功率晶体管

英飞凌BSC0402NS OptiMOS™5 150 V功率晶体管

特性

- 针对高性能 SMPS（例如同步整流）进行优化同步整流
- 100% 雪崩测试
- 卓越的耐热性
- N沟道
- 无铅镀层；符合RoHS标准
- 符合 IEC61249-2-21 标准的无卤素
- 低 Qrr 值

产品验证

符合 JEDEC 标准。

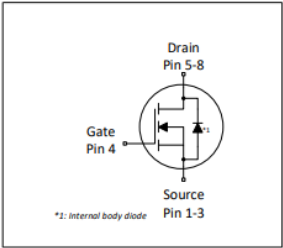
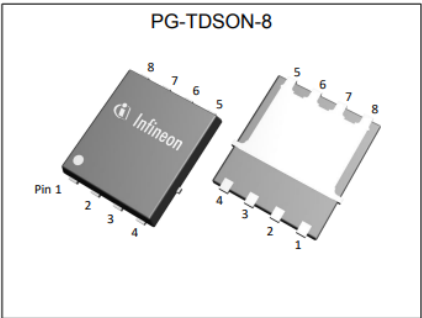


表 1 主要性能参数

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	9.3	mΩ
I_D	80	A
Q_{rr}	60	nC



Type / Ordering Code	Package	Marking	Related Links
BSC0402NS	PG-TDSON-8	0402NS	-

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目录

描述1

最大额定值3

热特性3

电气特性4

电气特性图6

封装外形10

修订记录11

商标11

免责声明11

1 最大额定值

除非另有规定, $T_A = 25\text{ °C}$

表 2 最大额定值

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	80 55	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	320	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	130	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	139	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 热特性

表3 热特性

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	0.54	0.9	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ³⁾	R_{thJA}	-	-	50	°C/W	-

¹⁾ 详细信息请参见图 3

²⁾ 详细信息请参见图 13

³⁾ 器件安装在 40 mm x 40 mm x 1.5 mm 环氧树脂印刷电路板 FR4 上, 漏极连接用铜面积为 6 cm² (一层, 70 µm 厚)。印刷电路板垂直放置在静止空气中。

3 电气特性

除非另有规定, $T_j = 25\text{ °C}$

表4 静态特性

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3.0	3.8	4.6	V	$V_{DS}=V_{GS}$, $I_D=107\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	7.9 8.7	9.3 10.5	m Ω	$V_{GS}=10\text{ V}$, $I_D=40\text{ A}$ $V_{GS}=8\text{ V}$, $I_D=20\text{ A}$
Gate resistance	R_G	-	1	1.5	Ω	-
Transconductance ¹⁾	g_{fs}	32	64	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=40\text{ A}$

表5 动态特性

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	2400	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	600	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	15	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	14	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=40\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	5	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=40\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=40\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	4	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=40\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

表6 栅极电荷特性²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	14	-	nC	$V_{DD}=75\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	7.0	-	nC	$V_{DD}=75\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	13.4	-	nC	$V_{DD}=75\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	33	-	nC	$V_{DD}=75\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.7	-	V	$V_{DD}=75\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	91	-	nC	$V_{DS}=75\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾由设计标定, 不受制于生产测试。

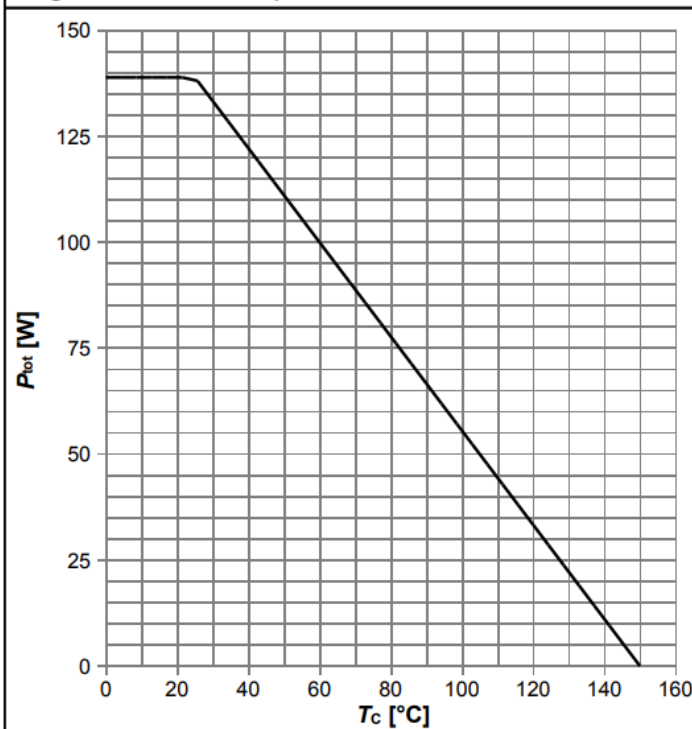
²⁾参数定义请参见“栅极电荷波形”

表 7 反向二极管

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	80	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	320	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.86	1.2	V	$V_{GS}=0\text{ V}$, $I_F=40\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time	t_{rr}	-	51	-	ns	$V_R=75\text{ V}$, $I_F=40\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	60	-	nC	$V_R=75\text{ V}$, $I_F=40\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

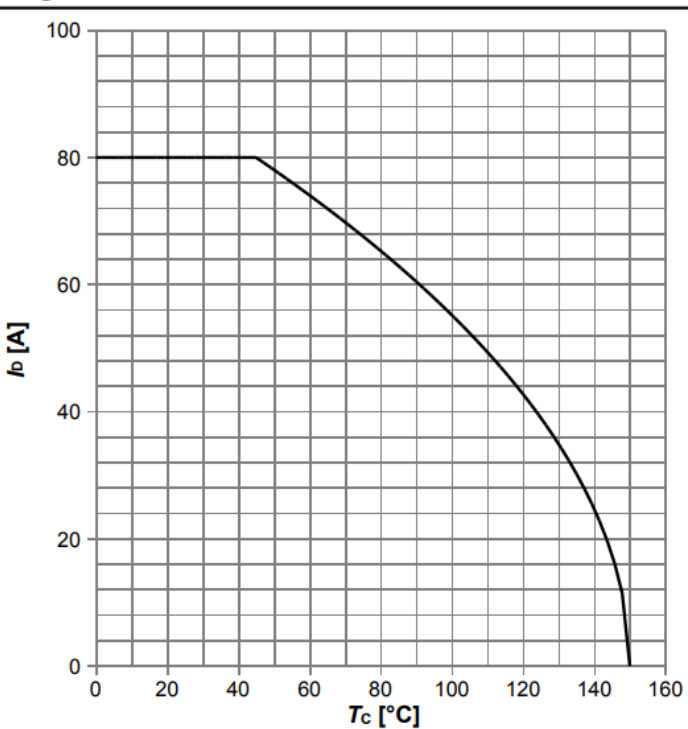
4 电气特性图

Diagram 1: Power dissipation



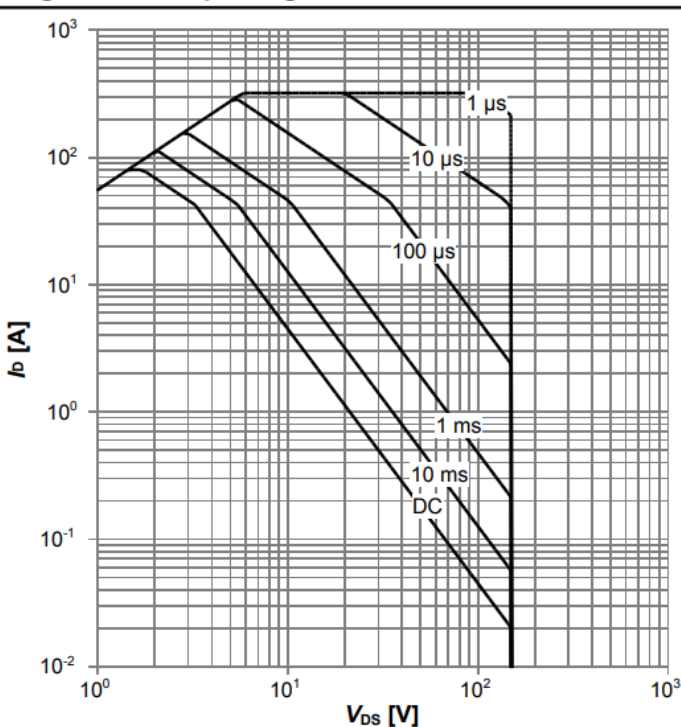
$$P_{tot}=f(T_c)$$

Diagram 2: Drain current



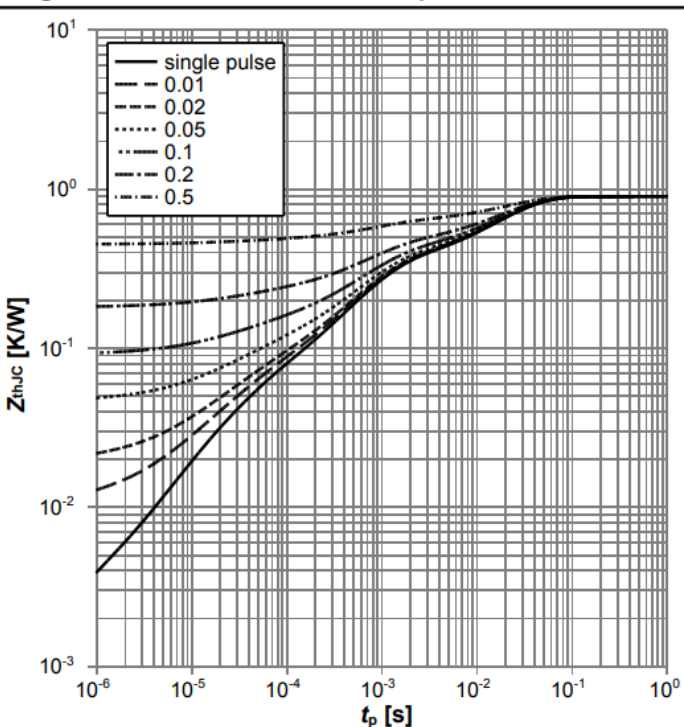
$$I_D=f(T_c); V_{GS}\geq 10\text{ V}$$

Diagram 3: Safe operating area



$$I_D=f(V_{DS}); T_c=25\text{ °C}; D=0; \text{ parameter: } t_p$$

Diagram 4: Max. transient thermal impedance



$$Z_{thJC}=f(t_p); \text{ parameter: } D=t_p/T$$

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BSC0402NS

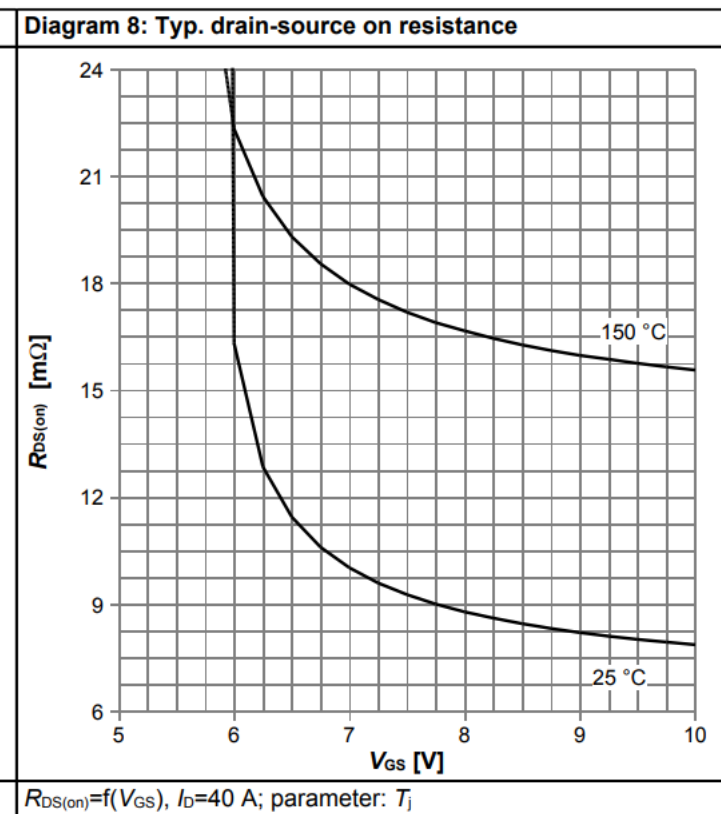
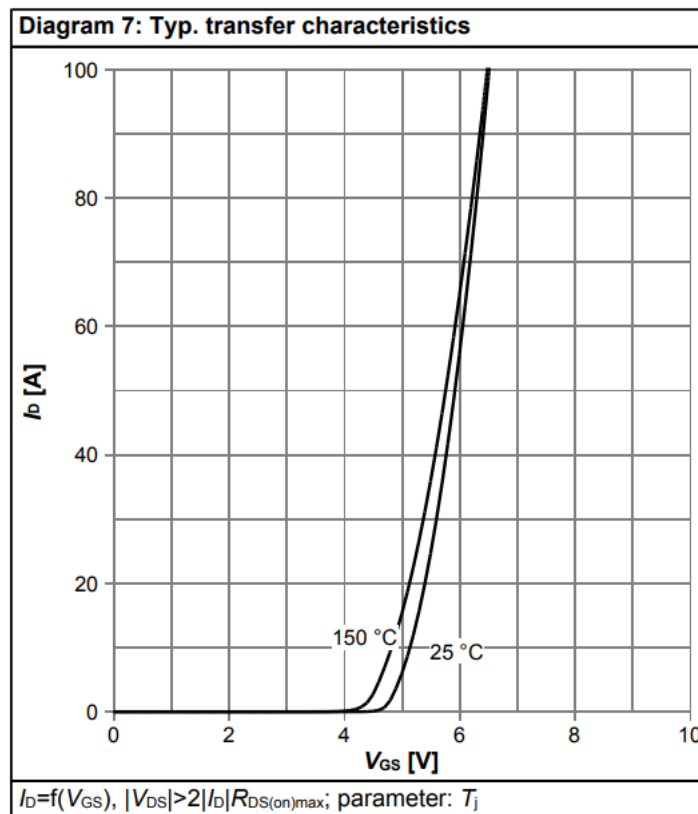
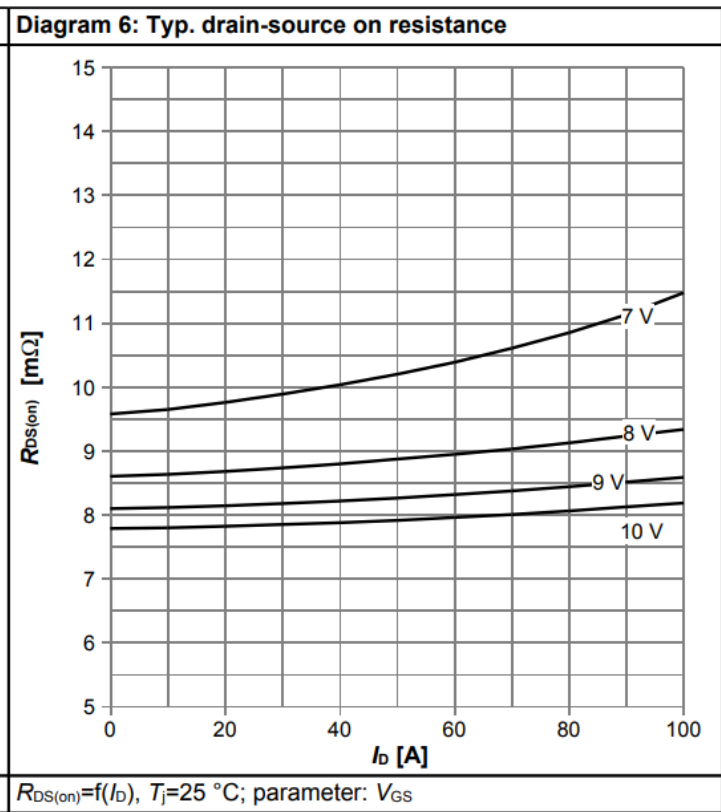
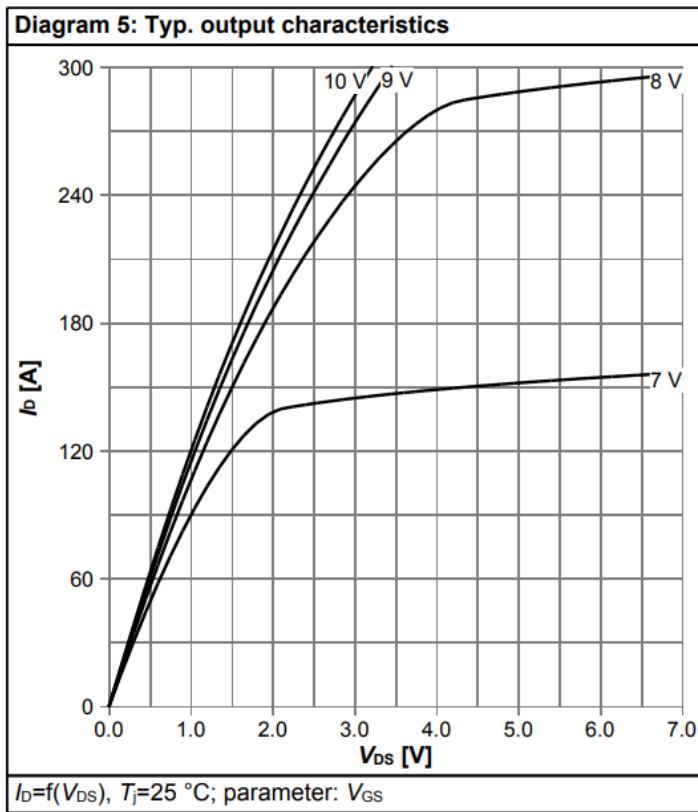
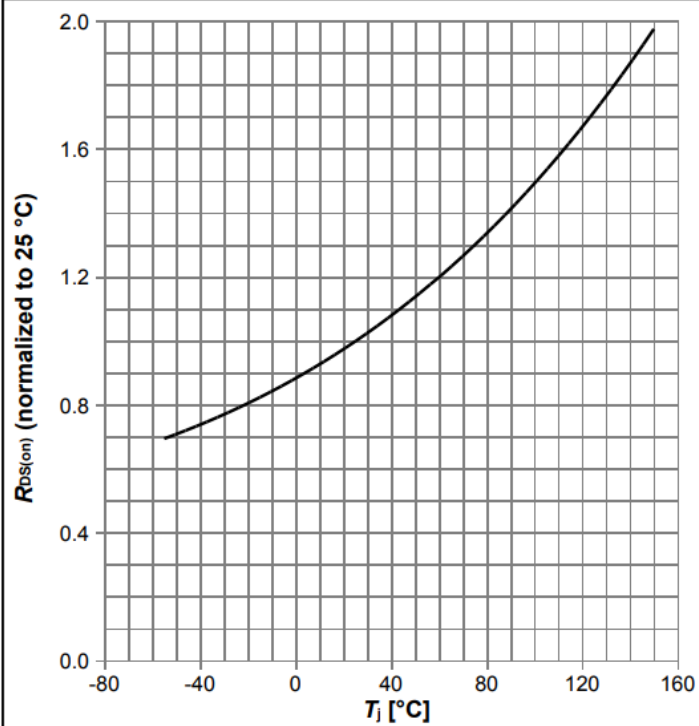
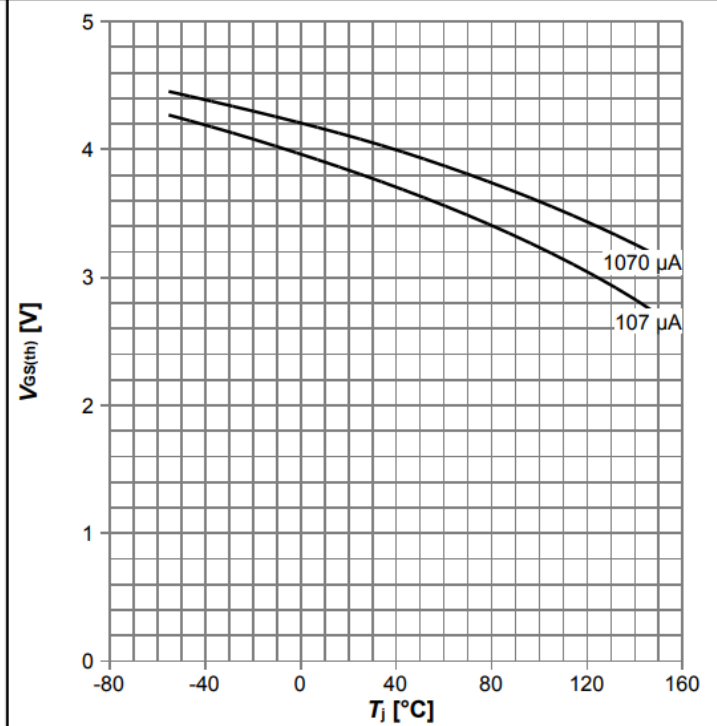


Diagram 9: Normalized drain-source on resistance



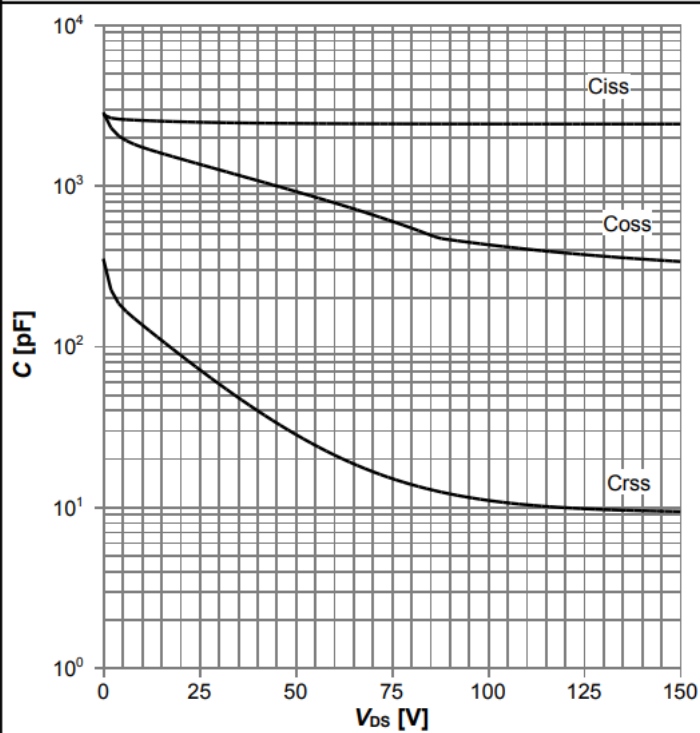
$R_{DS(on)} = f(T_j)$, $I_D = 40$ A, $V_{GS} = 10$ V

Diagram 10: Typ. gate threshold voltage



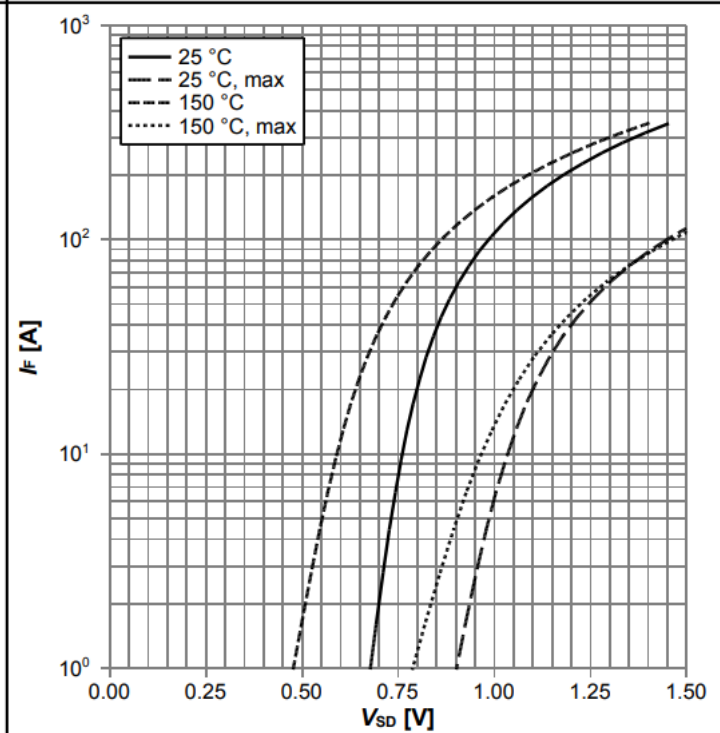
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



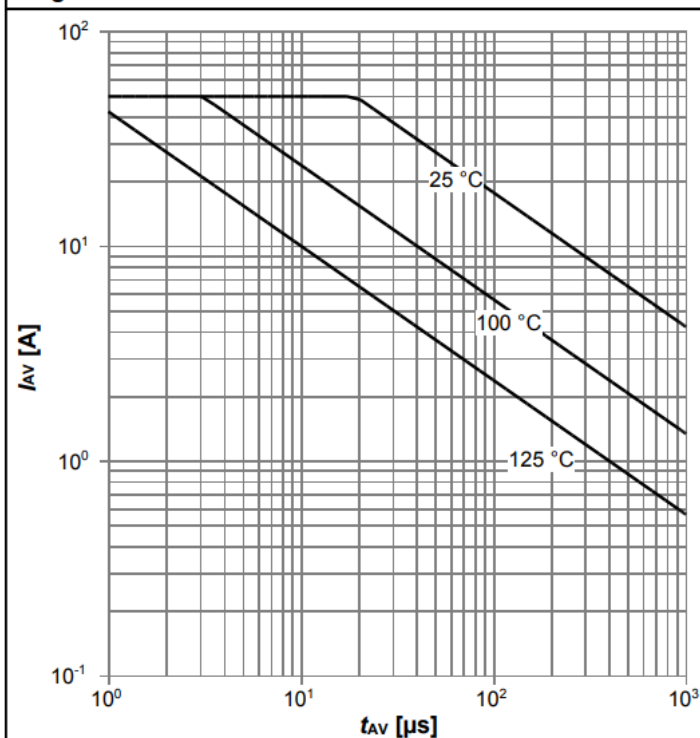
$C = f(V_{DS})$; $V_{GS} = 0$ V; $f = 1$ MHz

Diagram 12: Forward characteristics of reverse diode



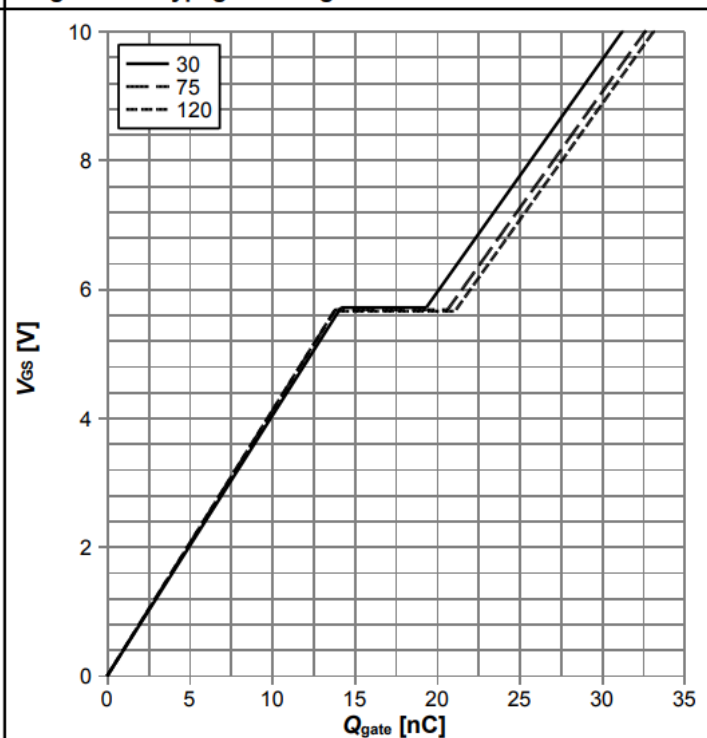
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



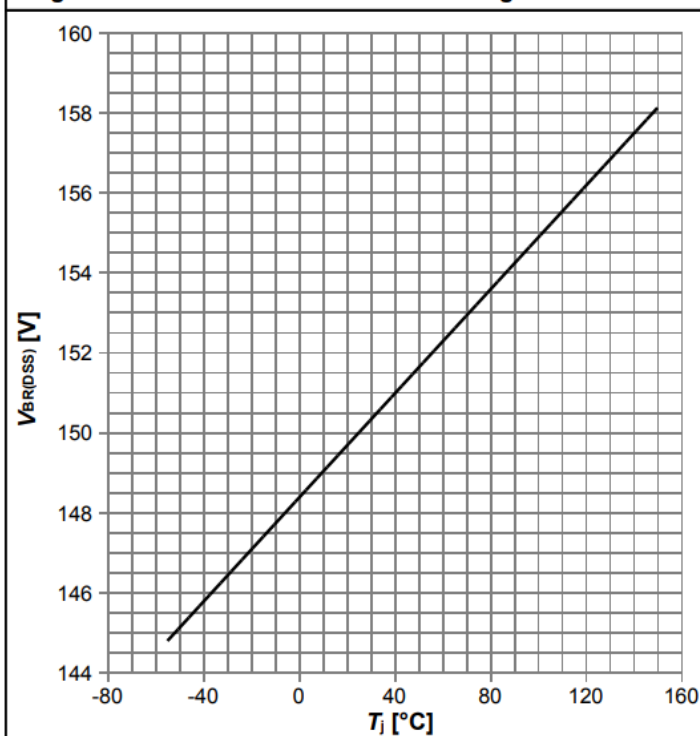
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



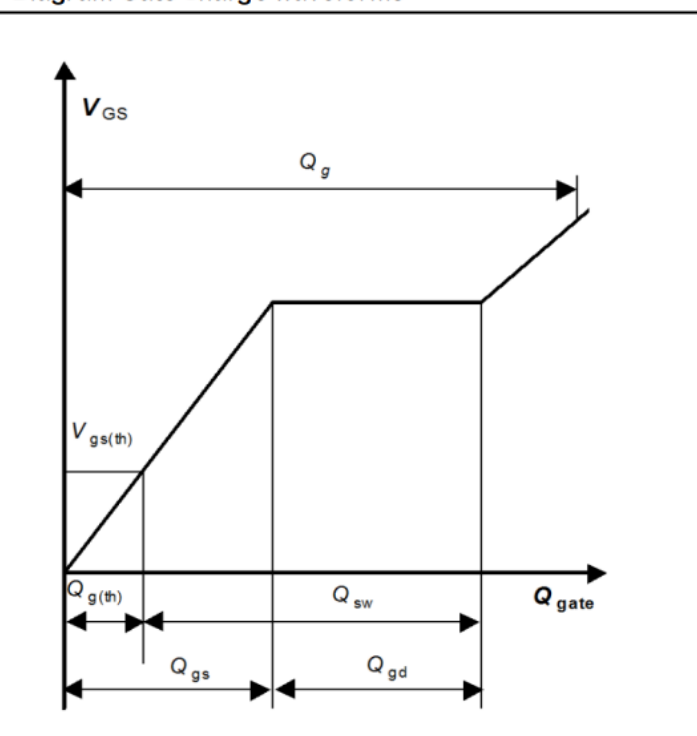
$V_{GS}=f(Q_{gate})$, $I_D=40\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

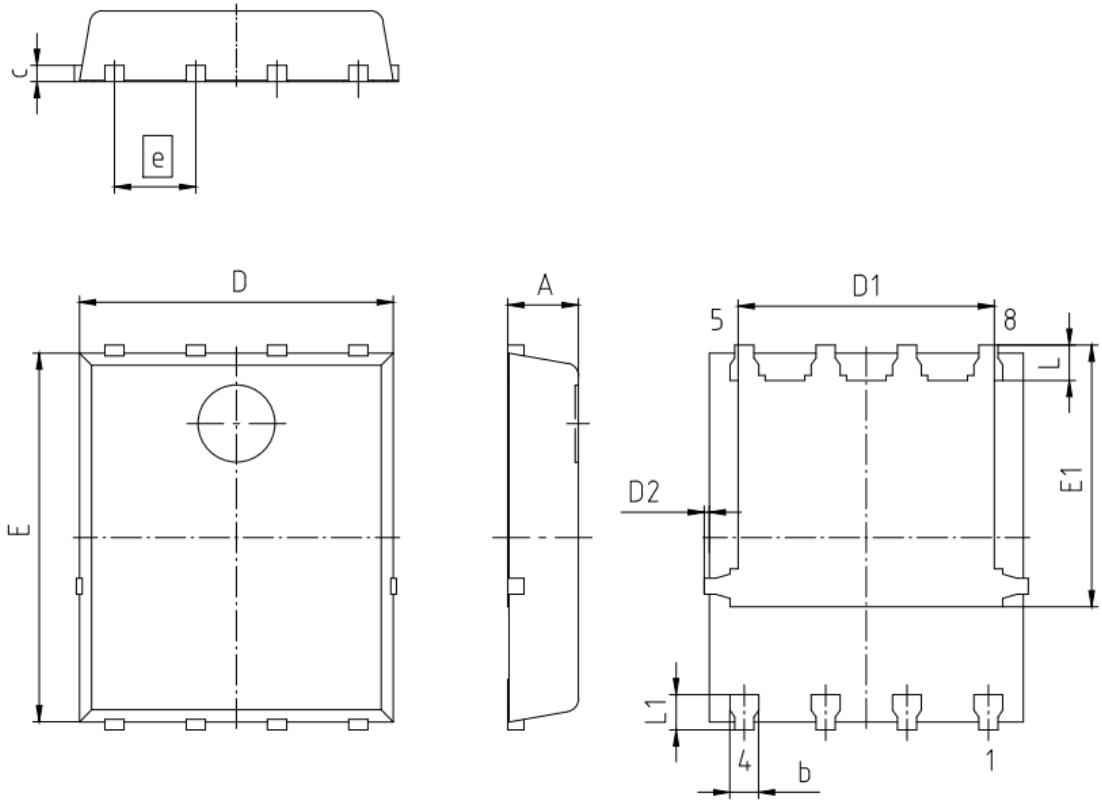
Diagram Gate charge waveforms



OptiMOS™5 Power-Transistor, 150 V

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5 封装外形



PACKAGE - GROUP NUMBER: PG-TDSON-8-U08		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
b	0.34	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.90	4.40
D2	0.00	0.22
E	5.70	6.10
E1	4.05	4.25
e	1.27	
L	0.45	0.65
L1	0.45	0.65

- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE
INTRUSION 0.1 MM
PROTRUSION 0.1 MM
- 3) ALL METAL SURFACES ARE PLATED,
EXCEPT AREA OF CUT

图1 PG-TDSON-8 外形图，尺寸单位为毫米

修订记录

BSC0402NS

Revision: 2022-11-08, Rev. 2.1

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.0	2019-12-16	Release of final version
2.1	2022-11-08	Update outline drawing and footnotes.

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